SANYO

No.2482

2 S C 4 1 6 1

NPN Triple Diffused Planar Type Silicon Transistor

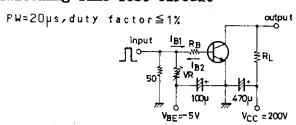
SWITCHING REGULATOR APPLICATIONS

Features

- . High breakdown voltage, high reliability
- DataSheet4U.com Fast switching speed (t_f=0.1µs typ)
 - . Wide ASO
 - . Adoption of MBIT process
 - . Micaless package facilitating mounting

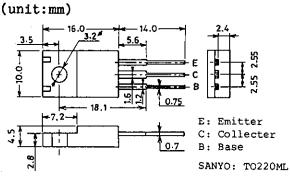
Absolute Maximum Ratings at Ta=25°C unit										
Collector-to-Base Voltage	У СВО		(500	V					
Collector-to-Emitter Voltag	e VCEO			400	v					
Emitter-to-Base Voltage	CEC	•		7	v					
Collector Current	V _{EBO}			7	Å					
Peak Collector Current	I _C	PW≤300µs,duty cyc]	A< 10%	14	Ā					
Base Current	icp	1 " 2 3 0 0 kg , daty cycl	-67 10%	3	A					
Collector Dissipation	I _B			2						
ooliootor bissipation	$\mathbf{P}_{\mathbf{C}}$	Te=25°C		-	W					
Junction Temperature	rr -:	16=25 6		30	o _C					
	Tj			150						
Storage Temperature	Tstg		-55 to +	150	°C					
Electrical Characteristics at Collector Cutoff Current Emitter Cutoff Current DC Current Gain Gain-Bandwidth Product	I _{CBO} I _{EBO} h _{FE1} h _{FE2} h _{FE3} f _T	V _{CB} =400V, I _E =0 V _{EB} =5V, I _C =0 V _{CE} =5V, I _C =0.8A V _{CE} =5V, I _C =4A V _{CE} =5V, I _C =10mA V _{CE} =10V, I _C =0.8A	min 15* 10 10	20	max 10 10 50#	unit µA µA				
Output Capacitance	c _{ob}	$V_{CB}^{-}=10V, f=1MHz$		80		pF				
C-E Saturation Voltage	VCE(sat)	$I_{C}=4A,I_{B}=0.8A$			0.8	V				
B-E Saturation Voltage	VBE(sat)				1.5	V				
C-B Breakdown Voltage	V(BR)CBO	$T^{L} = 1 \text{ my} \cdot T^{L} = 0$	500			V				
C-E Breakdown Voltage	V(BR)CEO		400			V				
E-B Breakdown Voltage	V(BR)EBO		7			V				
	(DICABDO	<u>д</u> - О	Continue	i on	next	page.				

Switching Time Test Circuit



Unit (Resistance : Ω , Capacitance : F)

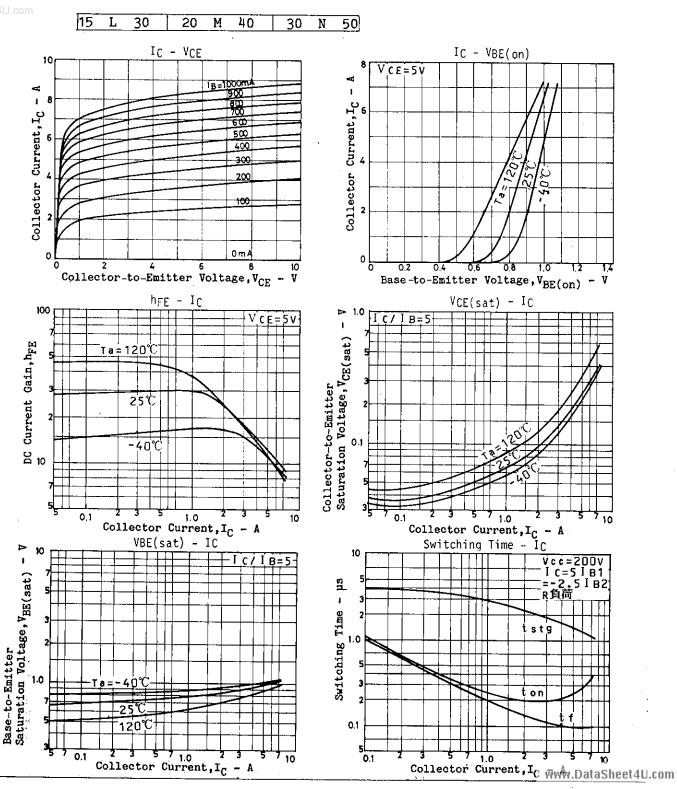
Pckage Dimensions 2041

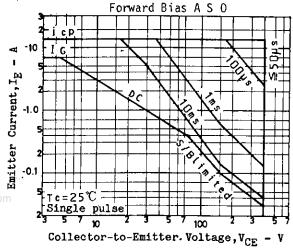


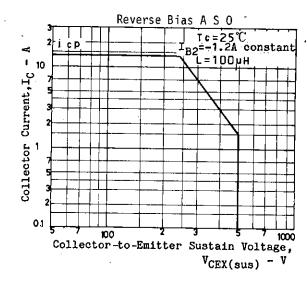
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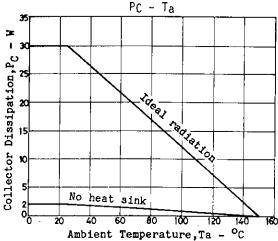
C-E Sustain Voltage	V _{CEX(sus)}	I _C =3A,I _{B1} =0.3A, I _{B2} =-1.2A,L=1mH,clamped	min 400	ty p	max	unit V
Turn-on Time	ton	I _{B2} =-1.2A, L= imh, clamped I _C =5A, I _{B1} =1A, I _{B2} =-2A, R _L =40ohms, V _{CC} =200V			0.5	μs
Storage Time Fall Time	tstg tf	n n			2.5 0.3	μs μs

The $h_{FE\,1}$ of the 2SC4161 is classified as follows. When specifying the $h_{FE\,1}$ rank, specify two ranks or more in principle.









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